- Space-Saving Package Option: Shrink Small-Outline Package (DB) Features EIAJ 0.65-mm Lead Pitch
- EPIC ™ (Enhanced-Performance Implanted CMOS) Submicron Process
- Designed to Facilitate Incident Wave Switching for Line Impedances of 50 Ω or Greater
- Typical V_{OLP} (Output Ground Bounce)
 < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C
- Typical V_{OHV} (Output V_{OH} Undershoot)
 2 V at V_{CC} = 3.3 V, T_A = 25°C
- ESD Protection Exceeds 2000 V Per MIL-STD-883C, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Latch-Up Performance Exceeds 250 mA Per JEDEC Standard JESD-17
- Package Options Include Plastic Small-Outline and Thin Shrink Small-Outline Packages

(TOP VIEW) 14 VCC 1A **1Y** 2 13 6A 12 6Y 2A 11 N 5A 2Y 10**∏** 5Y ЗА 9 AA **3Y** 6 8[] 4Y GND

D, DB, OR PW PACKAGE

description

This hex inverter is designed for 2.7-V to 3.6-V V_{CC} operation.

The SN74LVC04 contains six independent inverters. The device performs the Boolean function $Y = \overline{A}$.

The SN74LVC04 is packaged in TI's shrink small-outline package (DB), which provides the same I/O pin count and functionality of standard small-outline packages in less than half the printed-circuit-board area.

The SN74LVC04 is characterized for operation from -40°C to 85°C.

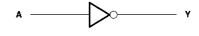
FUNCTION TABLE (each inverter)

INPUT	OUTPUT
A	Y
Н	L
L	н

logic symbol†

2 17 1A 2Δ 2Y 5 6 3A 9 8 4A 47 11 10 5A **5Y** 13 12 6A

logic diagram, each inverter (positive logic)



EPIC is a trademark of Texas Instruments Incorporated.



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V _{CC} 0.5 V to 4.6 V	V
Input voltage range, V _I (see Note 1)	
Output voltage range, V _O (see Notes 1 and 2)	V
Input clamp current, I_{IK} (V _I < 0)	Α
Output clamp current, I_{OK} ($V_O < 0$ or $V_O > V_{CC}$)	Α
Continuous output current, I _O (V _O = 0 to V _{CC}) ±50 mA	Α
Continuous current through V _{CC} or GND pins	Α
Maximum power dissipation at $T_A = 55^{\circ}C$ (in still air): D package	Ν
DB package 0.4 W	
PW package 0.4 W	
Storage temperature range	С

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions (see Note 3)

		MIN	MAX	UNIT
v_{cc}	Supply voltage	2.7	3.6	V
V_{IH}	High-level input voltage $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	2		V
V_{IL}	Low-level input voltage $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$		0.8	٧
V_1	Input voltage	0	Vcc	V
v _o	Output voltage	0	Vcc	٧
Іон	High-level output current V _{CC} = 2.7 V	П	-12	mA
	V _{CC} = 3 V		-24‡	
l _{OL}	Low-level output current		12	mA
	V _{CC} = 3 V		24‡	1114
Δt/Δν	Input transition rise or fall rate	0	10	ns/V
T _A	Operating free-air temperature	-40	85	°C

NOTE 3: Unused or floating inputs must be held high or low.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

^{2.} This value is limited to 4.6 V maximum.

[‡] Current duty cycle ≤ 50%, f ≥ 1 kHz

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST C	ONDITIONS	v _{cc} †	MIN	TYP	MAX	UNIT
V _{IK}	I ₁ = -18 mA	2.7 V			-1.2	٧	
	I _{OH} = -100 μA		MIN to MAX	V _{CC} -0.2			
V _{OH}	I _{OH} = -12 mA	2.7 V	2.2			v	
TOH	10H = - 12 HIA		3 V	2.4			
	I _{OH} = -24 mA		3 V	2			
	i _{OL} = 100 μA		MIN to MAX			0.2	
V_{OL}	I _{OL} = 12 mA		2.7 V			0.4	٧
	I _{OL} = 24 mA		3 V			0.55	
կ	V _I = V _{CC} or GND		3.6 V	1		±5	μA
loz	V _O = V _{CC} or GND		3.6 V	<u> </u>		±10	μА
lcc	$V_i = V_{CC}$ or GND,	I _O = 0	3.6 V			20	μА
ΔI _{CC}	V _{CC} = 3 V to 3.6 V, Other inputs at V _{CC} or GND	One input at V _{CC} – 0.6 V,			-	500	μΑ
Ci	V _I = V _{CC} or GND		3.3 V		TBD		pF
C _o	V _O = V _{CC} or GND		3.3 V		TBD		pF

[†] For conditions shown as MIN or MAX, use the appropriate values under recommended operating conditions.

